L Number	Hits	Search Text	DB	Time stamp
1	6	motohiro.inv. and ("MAIS")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:50
2	0	5233291.pn. and synthesis	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:08
3	0	5233291.pn. and switch$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:11
4	0	5233291.pn. and select$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:12
5	155	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:13
6	107	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and (switch$5 or select$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:15
7	54	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and ((switch$5 or select$5) same (capacit$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:28
8	122	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and ((switch$5 or select$5 or elect$5) same (capacit$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:30
9	68	(((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and ((switch$5 or select$5 or elect$5) same (capacit$5))) not (((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and ((switch$5 or select$5) same (capacit$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:30

-	46	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS")) same ((("C-V") or (CV)) near3 characteristic$5) same capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 12:03
-	37	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS")) and ("LCR" adj meter)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 11:46
-	1	"4083254".PN.	USPAT; US-PGPUB	2002/12/09 11:50
-	1	"4322979".PN.	USPAT; US-PGPUB	2002/12/09 11:50
-	1	"4681451".PN.	USPAT; US-PGPUB	2002/12/09 11:50
-	72	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS")) same ((("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) near3 characteristic$5) same capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:03
-	3	5701088.bi,uref.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 13:37
-	4	"6177826"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 12:34
-	23	"5175445"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 12:35
-	3	(("6177826") or ("5175445") or ("5107137")).PN.	USPAT; US-PGPUB	2002/12/09 12:35
-	14	5233291.bi,uref.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:00
-	2	5233291.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:03
-	1	"5065103".PN.	USPAT; US-PGPUB	2002/12/09 14:00
-	1	"4992728".PN.	USPAT; US-PGPUB	2002/12/09 14:01
-	1	"4941753".PN.	USPAT; US-PGPUB	2002/12/09 14:01
-	1	"4891584".PN.	USPAT; US-PGPUB	2002/12/09 14:01
-	154	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:05

-	155	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:12
-	12	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and synthesis	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:35
-	53	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and "nm"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:43
-	1	5233291.pn. and "MIS"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 15:29
-	2	5233292.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 15:30
-	2	5233291.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 15:43
-	0	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and (("4083254".PN. or three) adj nm)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 15:44
-	9	(("4083254".PN. or three) adj nm)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:14
-	1	5233291.pn. and MIS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:27
-	6860	motohiro.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:27
-	6828	motohiro.inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:28
-	6	motohiro.inv. and ("MAIS")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:50